

**18.** The process of claim **1** wherein the exposure is a patterned exposure.

**19.** The process of claim **18** wherein the pattern is created using a mask interposed between the source of the high resolution radiation, and the layer of resist material.

**20.** The process of claim **1** wherein the substrate is in the form of a wafer.

**21.** The process of claim **1** wherein the wafer is a silicon wafer.

**22.** A composition of matter suitable for use as a photoresist material, wherein said material is a strong absorber in the visible light range, such that in those areas of exposure to

visible light, the composition of matter undergoes a chemical change to thus modify its volatility, the contrast in volatility between the exposed and unexposed portions of the resist material sufficient to allow for the preferential volatilization of the exposed material under the influence of a laser light.

**23.** A dry lithography process in which:

- i) a resist layer is first deposited on a substrate;
- ii) the resist layer is exposed to an electron high resolution radiation beam to pattern the resist; and,
- iii) the patterned resist is thereafter dry developed with a laser to volatilize the resist in the areas of exposure.

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